

B.E. (Electronics and Communication Engineering)
Third Semester
EC-307: Electronics Devices and Circuits

Time allowed: 3 Hours

Max. Marks: 50

NOTE: Attempt five questions in all, including Question No. 1 which is compulsory and selecting two questions from each Section. Use of scientific calculator is allowed.

x-x-x

Q1. Answer the following: -

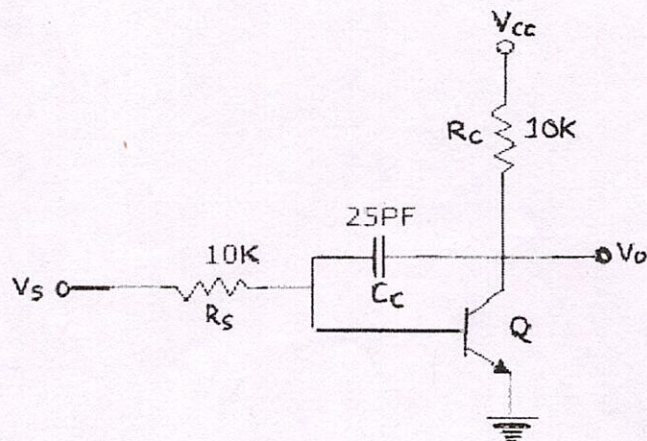
- (a) Why transistor is called current controlled device? (1)
- (b) What is power MOSFET? (1)
- (c) What is the theoretical maximum efficiency of a Class C amplifier? (1)
- (d) What is the significance of the arrow-head in the transistor symbol? (1)
- (e) Why silicon type transistors are more often used than germanium type? (1)
- (f) What is Shockley equation? (1)
- (g) Why is there a maximum limit of collector supply voltage for a transistor? (1)
- (h) How α and β are related to each other? (1)
- (i) What is the difference between output and transfer characteristics of the MOSFET? (1)
- (j) How does a thermistor's response time affect its performance? (1)

SECTION A

- Q2. (a)** (i) A germanium transistor is to be operated at zero signal $I_C = 1\text{mA}$. If the collector supply $V_{CC} = 12\text{V}$, what is the value of R_B in the base resistor method? Take $\beta = 100$. (5)
(ii) If another transistor of the same batch with $\beta = 50$ is used, what will be the new value of zero signal I_C for the same R_B ?
- (b)** In base bias method, how Q-point is affected by changes in V_{BE} and I_{CBO} . (5)
- Q3. (a)** What do you understand by 'Bias stability' of a transistor? Why is it necessary? (5)
Explain the working of self-bias circuit for common emitter BJT.
- (b)** What are the advantage and disadvantages of different thermistors. (5)
- Q4.** Annpn silicon transistor has $V_{CC} = 6\text{V}$ and the collector load $R_C = 2.5\text{k}\Omega$. Find: (10)
(i) The maximum collector current that can be allowed during the application of signal for faithful amplification.
(ii) (ii) The minimum zero signal collector current required

SECTION B

- Q5.** A common-emitter amplifier with an external capacitor C_C connected across the base and the collector of the transistor is shown in Figure. Determine the upper cutoff frequency f_H of the amplifier. ($g_m = 5\text{mA/V}$, $r_\pi = 200\text{k}\Omega$, $C_\pi = 1.5\text{pF}$ and $C_\mu = 0.5\text{pF}$) (10)



- Q6. (a)** Differentiate push pull and complementary symmetry class B amplifier. (5)
- (b)** An amplifier is assumed to have a single pole high frequency transfer function. The rise time of its output response to a step function input is 35 nsec. What is the upper 3 dB frequency (in MHz) for the amplifier to a sinusoidal input? (5)
- Q7. (a)** A 1 pF capacitor is available. Choose the inductor values in a Hartley oscillator so that $f = 1\text{MHz}$ and $m_v = 0.2$. (5)
- (b)** A JFET has the following parameters - $I_{DSS} = 32\text{mA}$; $V_{GS(off)} = -8\text{V}$; $V_{GS} = 4.5\text{V}$. Find the drain current. (5)

x-x-x